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Hwang

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(54) **ELECTROSTATIC DISCHARGE
PROTECTION CIRCUIT**

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H01L 29/87 (2006.01)

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27/0248 (2013.01)

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IPC H01L 27/0262, 27/0248

See application file for complete search history.

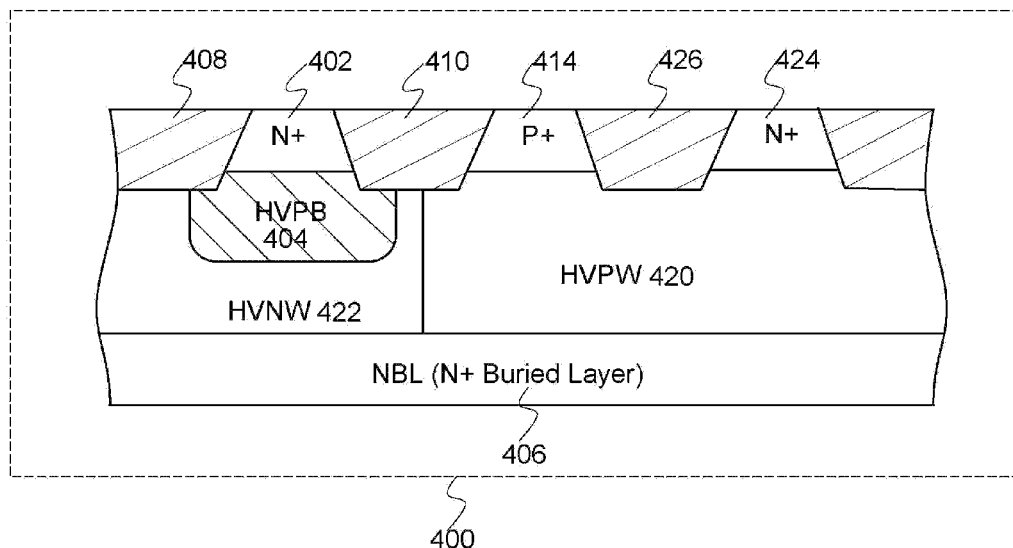
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(57) **ABSTRACT**

A device comprises a high voltage N well and a high voltage
P well over an N+ buried layer, a high voltage P-type
implanted region in the high voltage N well, a first N+ region
over the high voltage P-type implanted region and a P+ region
and a second N+ region over the high voltage P well.

18 Claims, 8 Drawing Sheets



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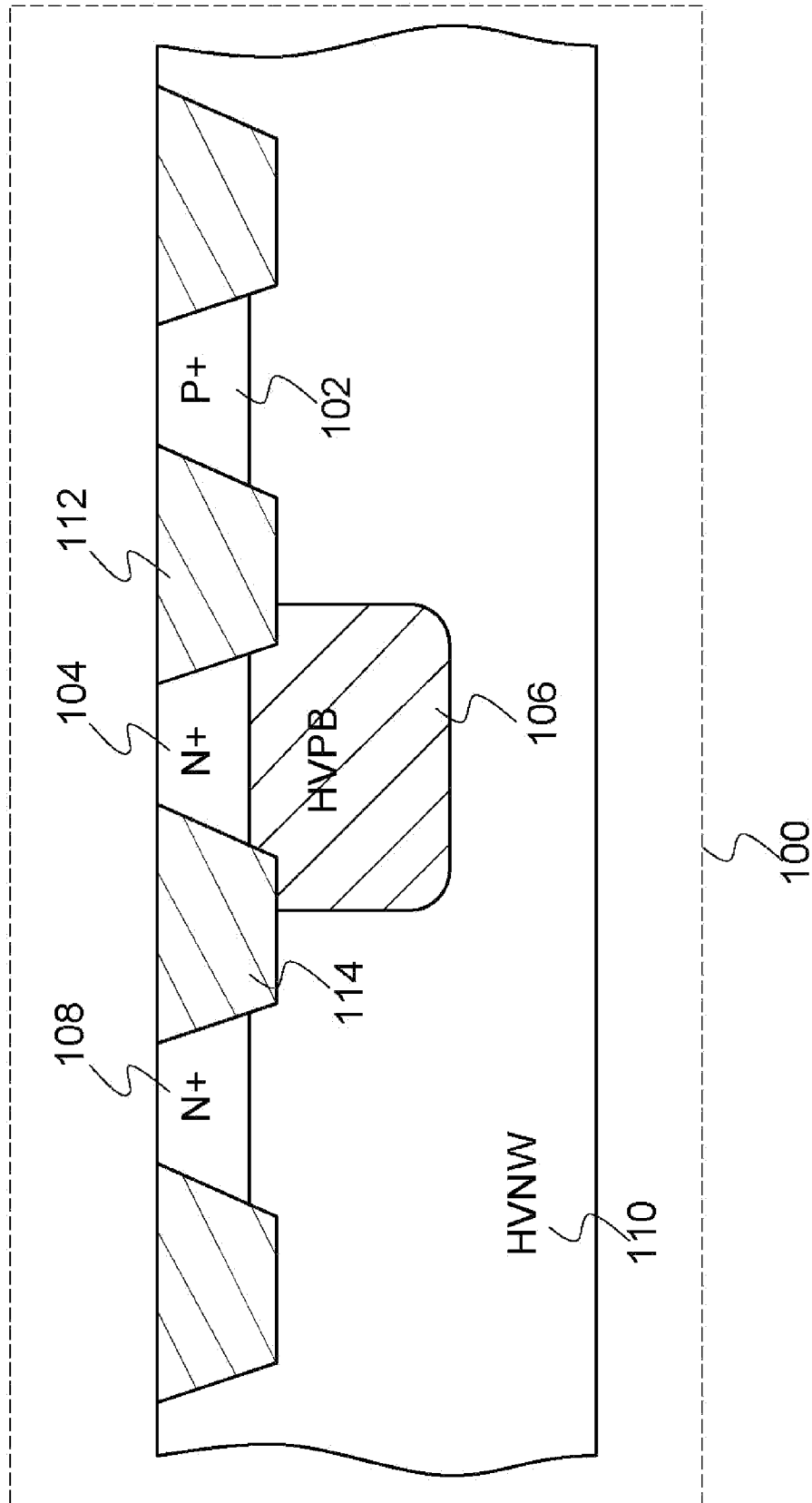


Figure 1

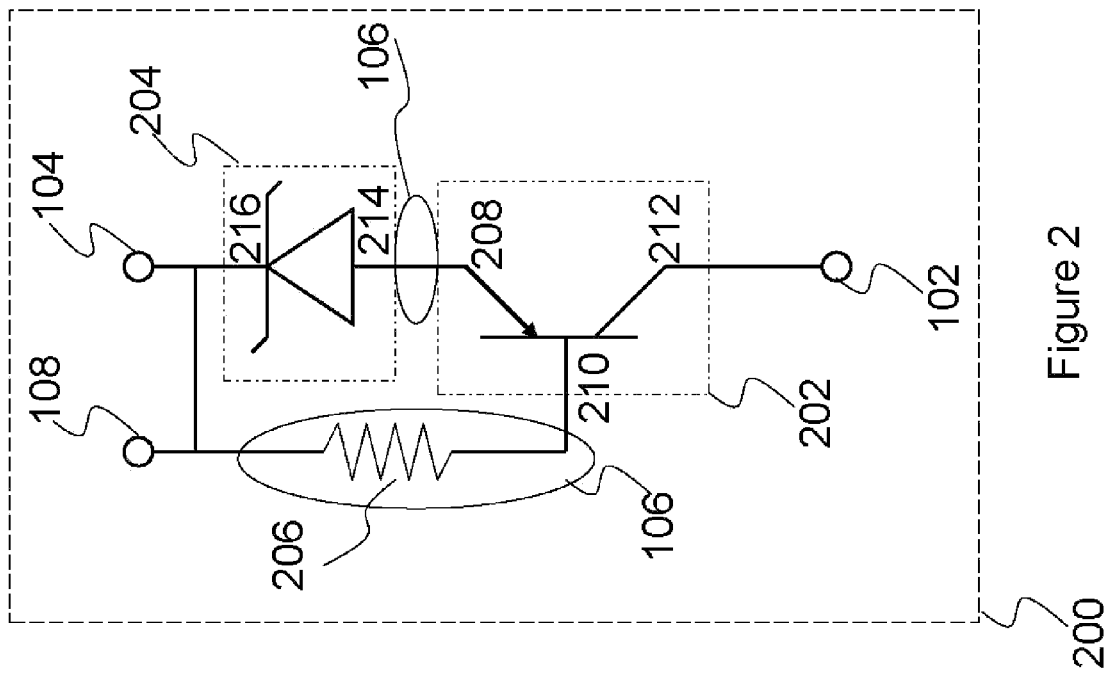


Figure 2

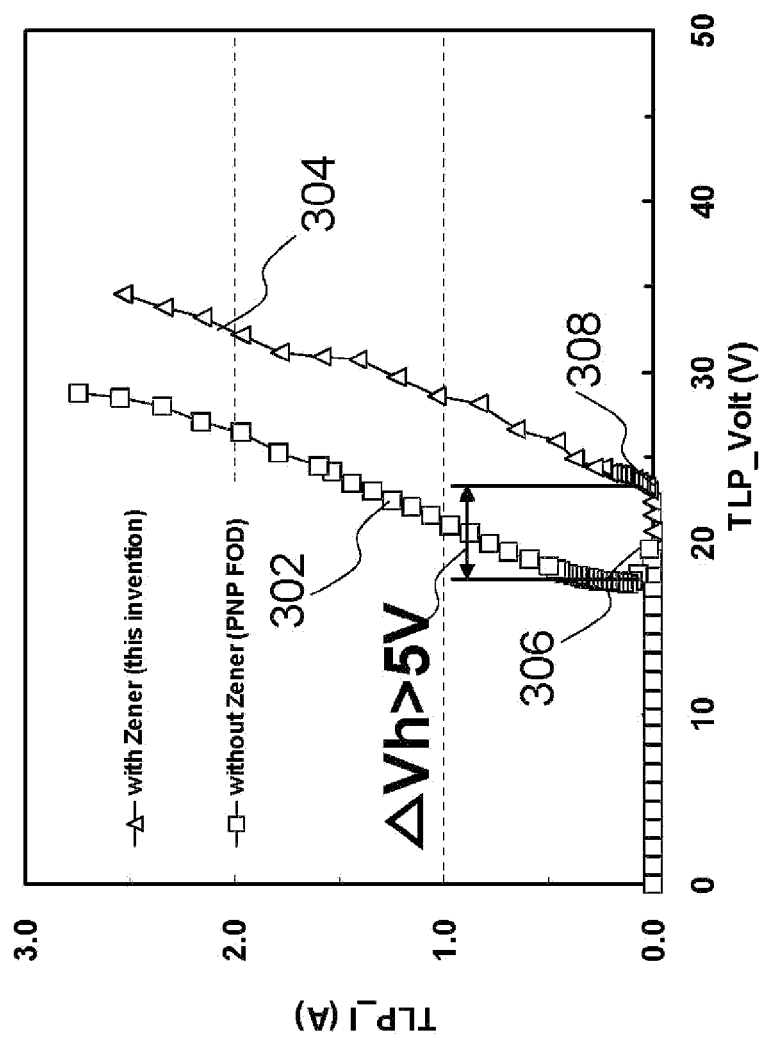


Figure 3

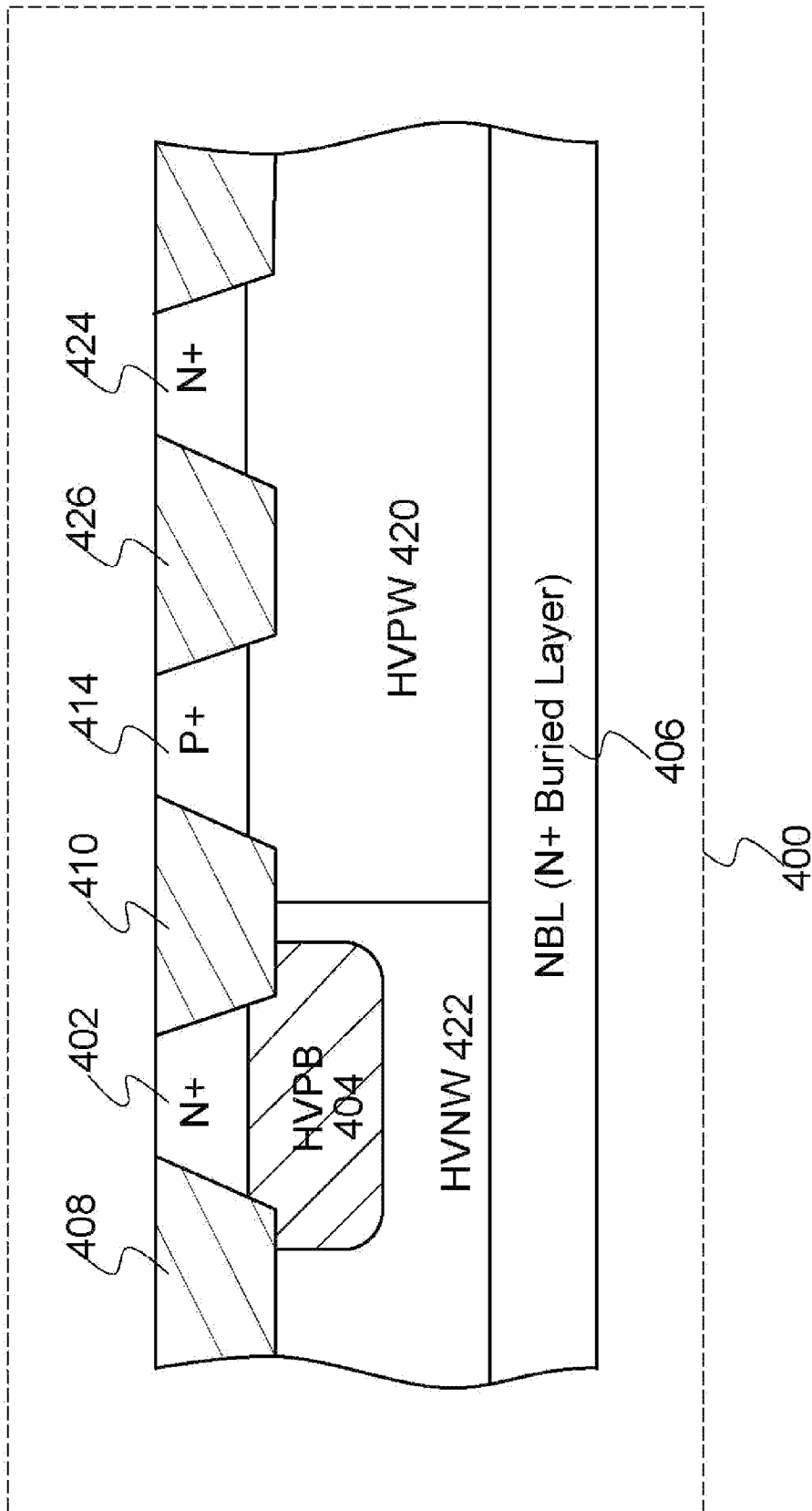


Figure 4

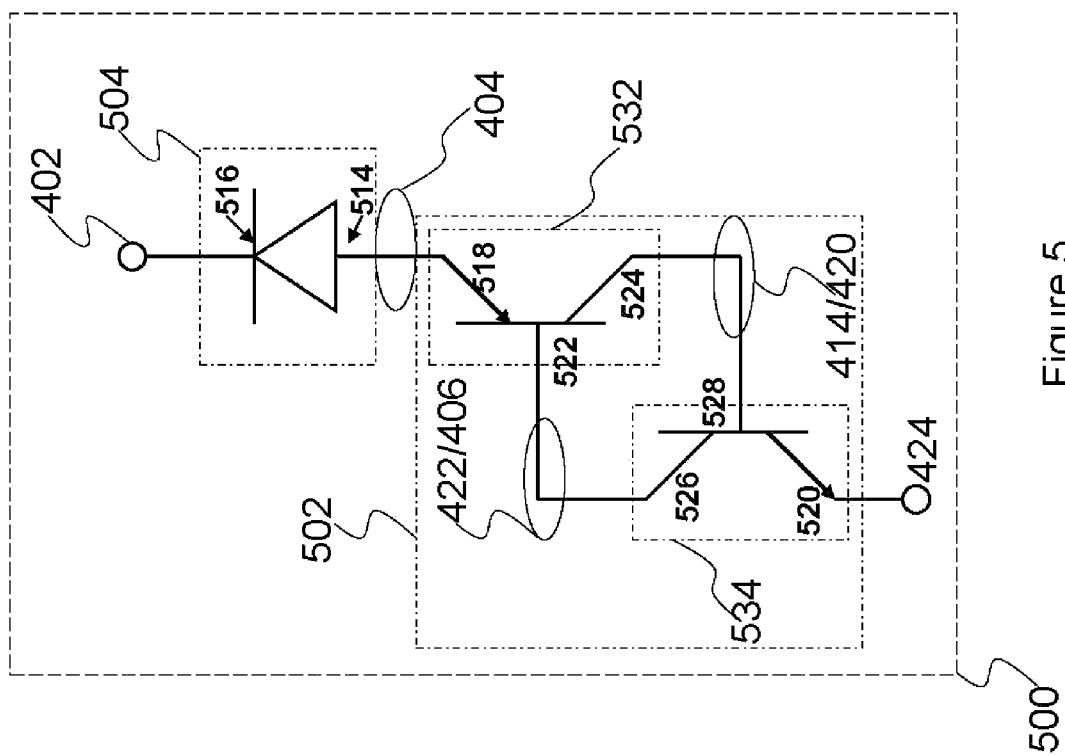


Figure 5

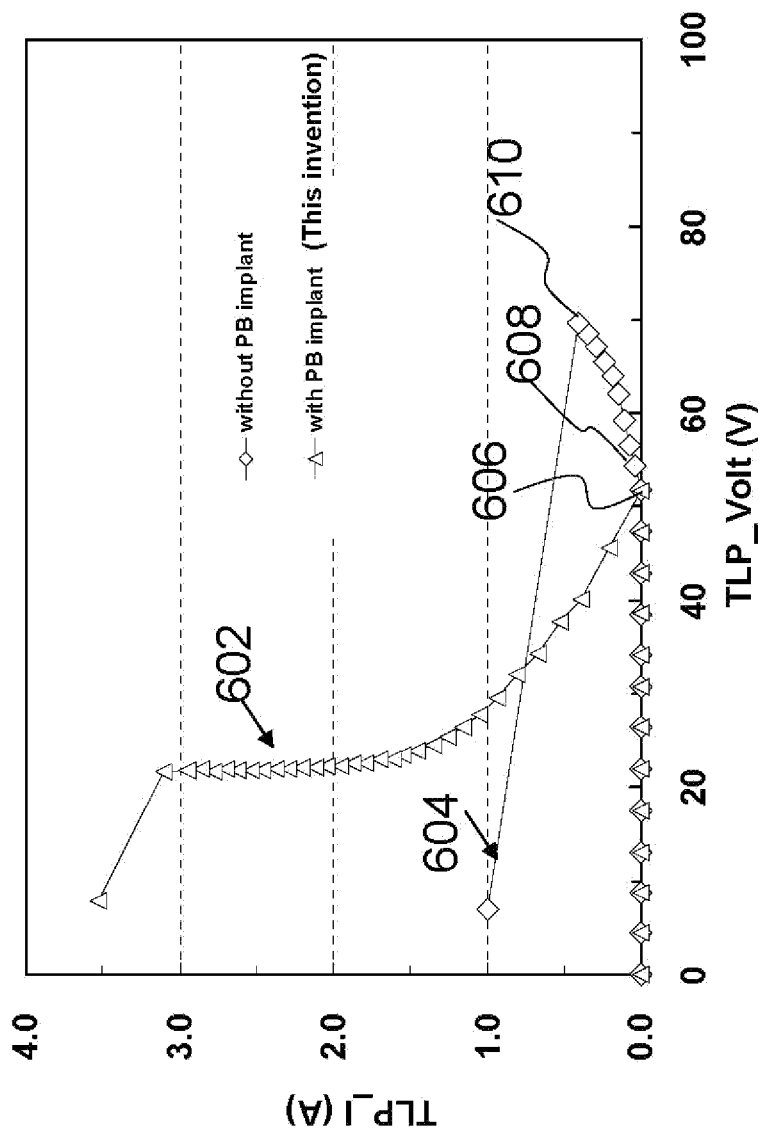


Figure 6

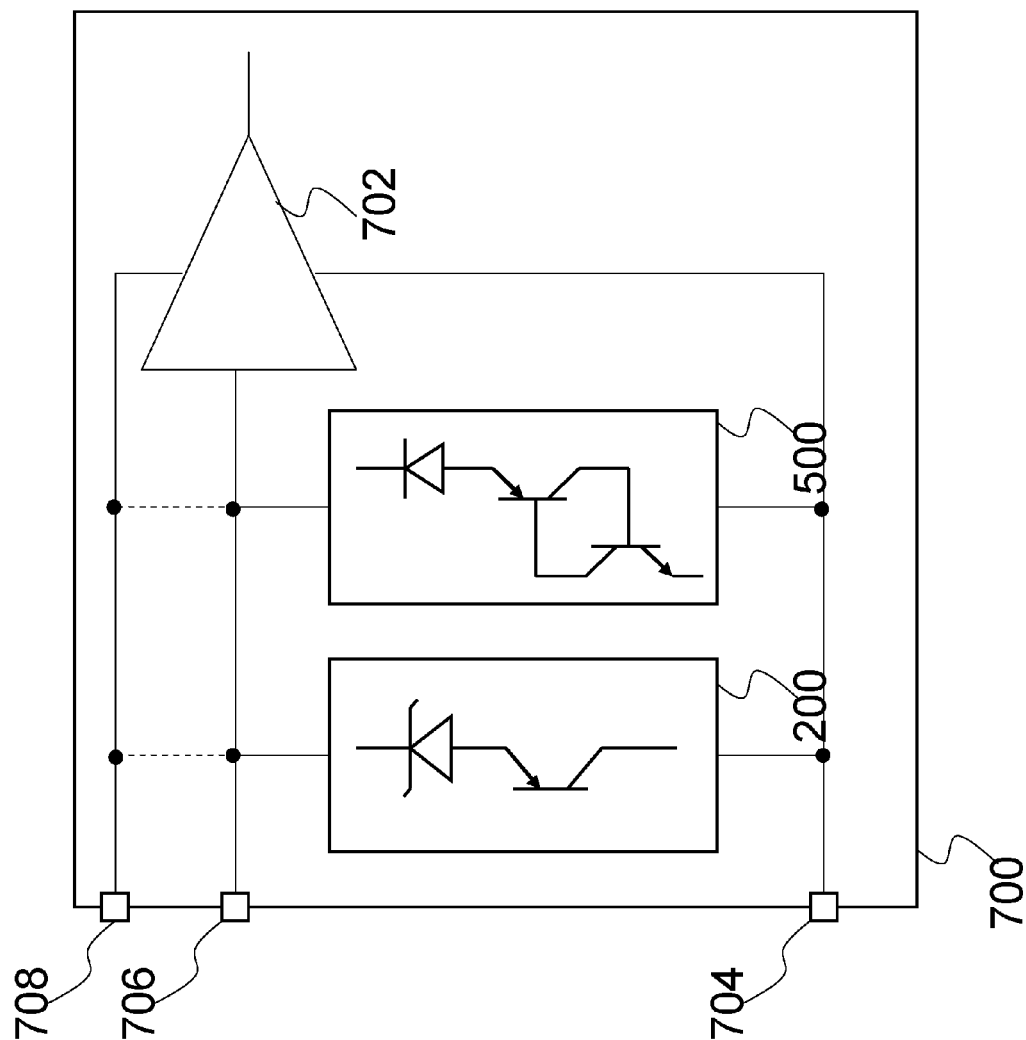


Figure 7

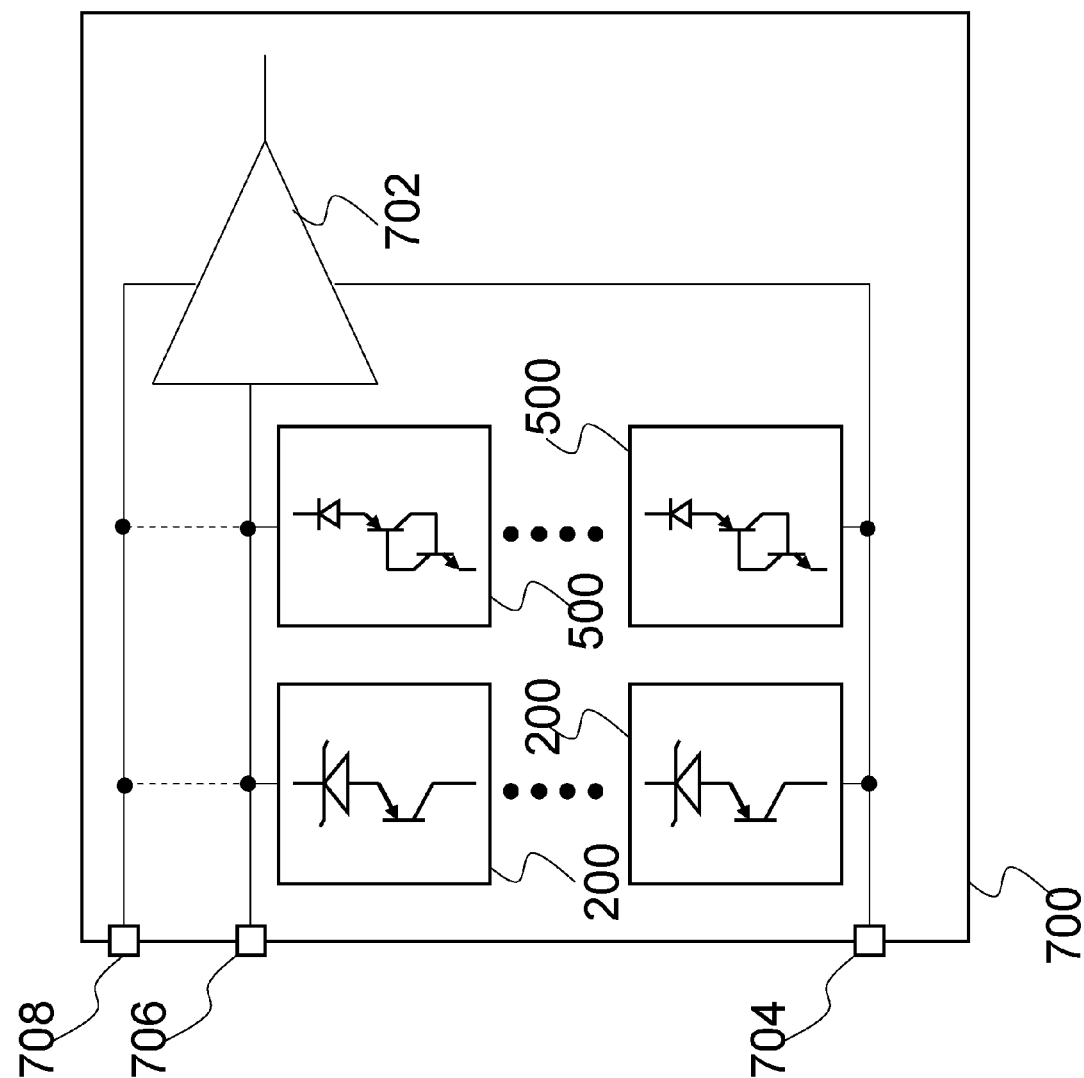


Figure 8

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ELECTROSTATIC DISCHARGE PROTECTION CIRCUIT

This application is a divisional of U.S. patent application Ser. No. 12/906,498, entitled "Electrostatic Discharge Protection Circuit," filed on Oct. 18, 2010, which application is incorporated herein by reference.

BACKGROUND

Electrostatic Discharge (ESD) is a rapid discharge that flows between two objects due to the built-up of static charge. ESD may destroy semiconductor devices because the rapid discharge can produce a relatively large current. In order to reduce the semiconductor failures due to ESD, ESD protection circuits have been developed to provide a current discharge path. When an ESD event occurs, the discharge current is conducted through the discharge path without going through the internal circuits to be protected.

In the semiconductor technology, NMOS transistors, Silicon-Controlled Rectifiers (SCRs) and RC triggered PMOS transistors are widely used. However, with the advance of submicron semiconductor processes, the existing ESD protection solutions may not meet the ever-increasing requirements from the semiconductor industry. For example, in a high voltage application, SCR or NMOS based ESD protection circuits may cause a latch-up failure because the holding voltage is not high enough. On the other hand, despite having a relatively high holding voltage, a RC triggered PMOS transistor may consume a large die area.

Accordingly, what is needed in the art is an ESD protection circuit having a high holding voltage. More particularly, the ESD protection circuit is capable of providing a reliable protection with an optimized semiconductor die size.

BRIEF DESCRIPTION OF THE DRAWINGS

For a more complete understanding of the present invention, and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which:

FIG. 1 illustrates a simplified cross section view of an ESD protection structure in accordance with an embodiment;

FIG. 2 illustrates an equivalent circuit diagram of the ESD protection structure illustrated in FIG. 1;

FIG. 3 illustrates I-V curves of a conventional ESD protection circuit and the ESD protection circuit in FIG. 2;

FIG. 4 illustrates a simplified cross section view of an ESD protection circuit in accordance with another embodiment;

FIG. 5 illustrates an equivalent circuit diagram of the ESD protection structure illustrated in FIG. 4;

FIG. 6 illustrates I-V curves of a conventional ESD protection circuit not having a high voltage P type implanted region and the ESD protection circuit in FIG. 5;

FIG. 7 illustrates an integrated circuit level ESD protection diagram; and

FIG. 8 illustrates a further ESD protection scheme by employing a plurality of ESD protection circuits in series connection.

Corresponding numerals and symbols in the different figures generally refer to corresponding parts unless otherwise indicated. The figures are drawn to clearly illustrate the relevant aspects of the various embodiments and are not necessarily drawn to scale.

DETAILED DESCRIPTION OF ILLUSTRATIVE EMBODIMENTS

The making and using of the presently preferred embodiments are discussed in detail below. It should be appreciated,

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however, that the present invention provides many applicable inventive concepts that can be embodied in a wide variety of specific contexts. The specific embodiments discussed are merely illustrative of specific ways to make and use the invention, and do not limit the scope of the invention.

FIG. 1 illustrates a simplified cross section view of an ESD protection structure 100 in accordance with an embodiment. The ESD protection structure 100 includes a P+ region 102, a first N+ region 104, a second N+ region 108, a first isolated region 112, a second isolated region 114, a high voltage P type implanted region 106 and a High Voltage N Well (HVNW) 110. The first N+ region 104 and the high voltage P type implanted region 106 are sequentially disposed on the HVNW 110. The high voltage P type implanted region 106 is disposed below the first N+ region 104. The P+ region 102 is disposed in the HVNW 110 at one side of the first N+ region 104. The P+ region 102 is separated from the first N+ region 104 by the first isolated region 112. The second N+ region 108 is disposed in the HVNW 110 at the other side of the first N+ region 104. The second N+ region 108 is separated from the first N+ region 104 by the second isolated region 114. For ESD protection applications, the first N+ region 104 is typically coupled to an input/output (I/O) pad and the P+ region 102 is typically coupled to a power supply VSS pad, which is typically grounded.

FIG. 2 illustrates an equivalent circuit diagram of the ESD protection structure 100 illustrated in FIG. 1. The equivalent circuit of the ESD protection structure illustrated in FIG. 1 includes a Zener diode 204, a bipolar PNP transistor 202 and a resistor 206. Referring again to FIG. 1, the high voltage P type implanted region 106 is disposed underneath the first N+ region 104. The junction between the high voltage P type implanted region 106 and the first N+ region 104 forms the Zener diode 204 as shown in FIG. 2. The Zener diode 204 has a cathode 216 and an anode 214. The cathode 216 is located in the first N+ region 104. The anode 214 is located in the high voltage P type implanted region 106. The Zener diode 204 has a typical breakdown voltage of 5V. Depending on the diffusion parameters of both the first N+ region 104 and the high voltage P type implanted region 106, the breakdown voltage of the Zener diode 204 can be up to 7V.

However, as one of ordinary skill in the art will recognize, the above described Zener diode 204 and its associated semiconductor structure is merely exemplary and is not intended to limit the present invention in any fashion. By selecting different diffusion parameters, any suitable Zener voltage rating may be utilized in the ESD protection circuit described above.

The bipolar PNP transistor 202 has an emitter 208, a base 210 and a collector 212. The emitter 208, the base 210 and the collector 212 are formed by the P+ region 102, the HVNW 110 and the high voltage P type implanted region 106 respectively (HVNW 110 is not shown but illustrated in FIG. 1). The emitter 208 is coupled to the anode 214 of the Zener diode 204. The base 210 is coupled to the second N+ region 108 through a resistor 206. The resistor 206 represents the parasitic resistance in the HVNW 110 (not shown but illustrated in FIG. 1). In sum, a simplified circuit diagram 200 depicts that the corresponding circuit of the ESD protection structure 100 is formed by a series connection of the Zener diode 204 and the bipolar PNP transistor 202.

However, it should be recognized that while FIG. 2 illustrates the ESD protection circuit with one Zener diode and one bipolar PNP transistor (e.g., Zener 204 and PNP transistor 202), the ESD protection circuit could accommodate any numbers of Zener diodes and bipolar PNP transistors. Furthermore, it is understood that the ESD protection circuit may

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be implemented using a plurality of Zener diodes or bipolar PNP transistors in series connection. On the other hand, other configurations of a plurality of Zener diodes and bipolar PNP transistors such as parallel-connected Zener diodes coupled to parallel-connected bipolar PNP transistors are also within the contemplated scope of this embodiment.

As known in the art, the bipolar PNP transistor **202** has a breakdown voltage. When a large voltage spike is applied between the emitter **208** and the collector **212**, the bipolar PNP transistor **202** may experience an avalanche breakdown in which a large current is allowed to flow from the emitter **208** to the collector **212**. The current path from the emitter **208** to the collector **212** may provide a bypass of the ESD current and clamp the voltage between the emitter **208** and the collector **212** to a level below the maximum rating voltage of the internal circuit, so that it helps to prevent the large voltage spike from damaging the internal circuits being protected. Similarly, the Zener diode **204** has a breakdown voltage (e.g., 5V) when a voltage is applied between the cathode **216** and the anode **214**. In sum, the ESD protection circuit **200** has a breakdown voltage equivalent to the bipolar PNP transistor's **202** breakdown voltage plus the Zener's **204** breakdown voltage.

The ESD protection circuit **200** is typically placed at an I/O pad and a VSS of a device to be protected (not shown but illustrated in FIG. 7). The first N+ region **104** is typically coupled to the I/O pad and the P+ region **102** is typically coupled to the VSS, which is typically grounded. If an ESD event occurs, a voltage spike is applied between the first N+ region **104** and the P+ region **102**. Firstly, both the Zener diode **204** and the bipolar PNP transistor **202** experience the voltage spike, which may exceed both the Zener diode **204** and the bipolar PNP transistor **202**'s breakdown voltages. The Zener diode **204** allows the ESD current to flow from the cathode **216** to the anode **214** when the voltage across the cathode **216** and the anode **214** exceeds the Zener diode's **204** breakdown voltage (e.g., 5V). In addition, the Zener diode **204** may clamp the voltage between the cathode **216** and the anode **214** to its breakdown voltage (e.g., 5V).

Furthermore, if the voltage spike minus 5V still exceeds the breakdown voltage of the bipolar PNP transistor **202**, the bipolar PNP transistor **202** enters an avalanche conduction mode. Consequently, the bipolar PNP transistor provides a current path so that the ESD discharge current can flow from the emitter **208** to the collector **212**. The conduction of both the Zener **204** and the bipolar PNP **202** clamps the voltage between the cathode **216** and the collector **212** to a lower level so that the internal circuits coupled to the cathode **216** can be protected.

It should be noted that both the Zener diode **204** and the bipolar PNP transistor **202** may turn on nearly simultaneously. However, for convenience the description above uses a slightly earlier turn-on of the Zener diode **204** as an example to describe the breakdown mechanism. It is understood that the turn-on sequence between the Zener diode **204** and the bipolar PNP transistor **202** plays no role in this embodiment. The breakdowns of two series-connected elements (e.g., Zener diode **204** and PNP transistor **202**) in the ESD protection circuit **200** may be performed in any arbitrary sequence. However, the specifically discussed example above is preferred.

Referring again to FIG. 2, the base **210** is coupled to the cathode **216** through a resistor **206**. In this embodiment, the resistor **206** represents the body resistance of the HVNW **110**. It should be noted that the resistance between the base **210** and the emitter **208** may have an impact on the collector-emitter breakdown voltage of the bipolar PNP transistor **202**.

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The direct connection between the second N+ region **108** and the first N+ region **104** is provided for illustrative purpose only, and is provided only to provide an example of the functionality that may be included in this embodiment. One of ordinary of skill in the art will realize that in ESD protection applications, the second N+ region **108** may be floating or coupled to the first N+ region through an external resistor outside the ESD protection structure **100**.

FIG. 3 illustrates I-V curves of a conventional ESD protection circuit such as a PNP field oxide device and the ESD protection circuit **200** in FIG. 2. The horizontal axis of FIG. 3 represents the ESD voltage across an ESD protection circuit (e.g., the ESD protection circuit **200**). The vertical axis of FIG. 3 represents the ESD current flowing through the ESD protection circuit. A curve **302** illustrates the current flowing through a conventional ESD protection circuit as a voltage spike is applied. A square on the curve **302** indicates a corresponding ESD voltage at the horizontal axis and a corresponding ESD current at the vertical axis. As shown in FIG. 3, a square **306** indicates a breakdown voltage for a conventional ESD protection circuit. On the curve **302**, before the applied voltage reaches the square **306**, the ESD current is approximately equal to zero. Once the applied ESD voltage exceeds the square **306** where the corresponding ESD voltage is about 18V, the ESD current increases in proportion to the applied ESD voltage. In this embodiment, the peak ESD current of the conventional ESD protection circuit is up to about 3 A with a holding voltage approximately 30V.

The curve **304** represents the I-V relationship for the ESD protection circuit **200** during an ESD test. Similarly, the isosceles triangles on the curve **304** indicate the I-V relationship of the ESD protection circuit **200**. An isosceles triangle **308** as shown in FIG. 3 indicates the breakdown voltage of the ESD protection circuit **200** (approximately 23V as illustrated in FIG. 3). After a resulting breakdown, the curve **304** is about in parallel with the curve **302** but having a voltage gap, which is about 5V as illustrated in FIG. 3. An advantageous feature of the described embodiment is the Zener diode **204** helps to provide a higher ESD breakdown voltage.

FIG. 4 illustrates a simplified cross section view of an ESD protection structure **400** in accordance with another embodiment. The ESD protection structure **400** includes a first N+ region **402**, a P+ region **414**, a second N+ region **424**, a first isolated region **408**, a second isolated region **410** and a third isolated region **426**. The first N+ region **402** is isolated from the P+ region **414** by the second isolated region **410**. Likewise, the second N+ region **424** is separated from the P+ region **414** by the third isolated region **426**. The ESD protection structure **400** further includes a high voltage P type implanted region (HVPB) **404**, a HVNW **422**, a High Voltage P Well (HVPW) **420** and an N+ Buried Layer (NBL) **406**. The high voltage P type implanted region **404** and the first N+ region **402** are sequentially disposed on the HVNW **422**. The high voltage P type implanted region **404** is disposed below the first N+ region **402**. Both the P+ region **414** and the second N+ region **424** are disposed in the HVPW **420**. Both the HVNW **422** and HVPW **420** are disposed on the NBL **406**. For ESD protection applications, the first N+ region **402** is typically coupled to an input/output (I/O) pad and the second N+ region **424** is typically coupled to a power supply VSS pad, which is typically grounded.

FIG. 5 illustrates an equivalent circuit diagram of the ESD protection structure **400** illustrated in FIG. 4. The equivalent circuit includes a reverse diode **504** and a Silicon-Controlled Rectifier (SCR) **502**. As described above, the first N+ region **402** is disposed on top of the high voltage P type implanted region **404**. The junction between the high voltage P type

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implanted region **404** and the first N+ region **402** forms the reverse diode **504**. The reverse diode **504** has a cathode **516** and an anode **514**. The cathode **516** is located in the first N+ region **402**. The anode **514** is located in the high voltage P type implanted region **504**. The breakdown voltage of the reverse diode **504** may depend on several semiconductor diffusion parameters, such as the doping density of the high voltage P type implanted region **404**.

The SCR **502** includes a bipolar PNP transistor **532** having a first emitter **518**, a first base **522** and a first collector **524**, and a bipolar NPN transistor **534** having a second emitter **520**, a second base **528** and a second collector **526**. The first emitter **518**, the first base **522** and the first collector **524** are formed by the high voltage P type implanted region **404**, the HVNW **422** and the HVPW **420** respectively (not shown but illustrated in FIG. 4). The second collector **526**, the second base **528** and the second emitter **520** are formed by the HVNW **422**, the HVPW **420** and the second N+ region **424** respectively (not shown but illustrated in FIG. 4). As shown in FIG. 5, the first base **522** of the bipolar PNP transistor **532** is tied to the second collector **526** of the bipolar NPN transistor **534**, and the second collector **524** of the bipolar PNP transistor **532** is tied to the second base **528** of the bipolar NPN transistor **534**. The SCR **502**, as an independent block typically has two terminals (e.g. the first emitter **518** and the second emitter **520**) exposed to the outside circuits. In this embodiment, the first emitter **518** is coupled to the anode **514**. The second emitter **520** is coupled to the second N+ region **424**. In sum, a simplified equivalent circuit diagram **500** illustrates an ESD protection circuit having a reverse diode **504** in series connection with the SCR **502**.

As known in the art, the SCR (e.g., the SCR **502** shown in FIG. 5) has a characteristic called "snapback," which means that when a high voltage spike is applied to an SCR, the SCR may be turned on. In FIG. 5, the SCR **502** may be turned on after a voltage spike is applied between the first emitter **518** and the second emitter **520**. The ESD current flows through the SCR **502**, so that the voltage between the first emitter **518** and the second emitter **520** snaps back and is lowered. The voltage across the SCR **502** after a snapback may be partially determined by the doping densities in the HVNW **422** and HVPW **420** (not shown but illustrated in FIG. 4). The lower voltage across the SCR **502** may prevent the large voltage spike from damaging the internal circuits being protected.

The ESD protection circuit **500** is typically placed at an I/O pad and a VSS of a device to be protected. In FIG. 5, the first N+ region **402** is typically coupled to the I/O pad and the second N+ region **424** is typically coupled to the VSS, which is typically grounded. If an ESD event occurs, a voltage spike is applied between the first N+ region **402** and the second N+ region **424**. Firstly, both the reverse diode **504** and the SCR **502** experience the voltage spike, which exceeds both the reverse diode **504** and the SCR **502**'s breakdown voltages. The reverse diode **504** allows the ESD current to follow from the cathode **516** to the anode **514** when the voltage across the cathode **516** and the anode **514** exceeds the reverse diode's **504** breakdown voltage (e.g., 5V).

Furthermore, if the voltage spike minus 5V still exceeds the breakdown voltage of the SCR **502**, the SCR **502** enters the snapback mode. Consequently, the SCR **502** provides a current path so that the ESD discharge current flows into the first emitter **518** and flows out of the second emitter **520**. Meanwhile, the breakdowns of both the SCR **502** and the reverse diode **504** clamps the voltage across the ESD protection circuit **500** to a lower voltage level so that the circuits coupled to the ESD protection circuit **500** are protected.

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It should be noted that both the SCR **502** and the reverse diode **504** turn on nearly simultaneously. For convenience, the description above assumes that the reverse diode **504** turns on slightly earlier than the SCR **502**. This turn-on sequence is merely exemplary and is not intended to limit the present invention in any fashion. Any suitable turn-on sequence between the SCR **502** and the reverse diode **504** may be included in this embodiment.

FIG. 6 illustrates I-V curves of a conventional ESD protection circuit and the ESD protection circuit **500**. The horizontal axis of FIG. 6 represents the ESD voltage across an ESD protection circuit (e.g., the ESD protection circuit **500**). The vertical axis of FIG. 6 represents the ESD current flowing through the ESD protection circuit. A curve **604** illustrates the current flowing through a conventional ESD protection circuit as a voltage spike is applied. A diamond on the curve **604** indicates a corresponding ESD voltage at the horizontal axis and a corresponding ESD current at the vertical axis.

As shown in FIG. 6, a diamond **608** indicates a breakdown voltage for a conventional ESD protection circuit (approximately 53V as illustrated in FIG. 6). On the curve **604**, before the applied voltage reaches the diamond **608**, the ESD current is approximately equal to zero. Once the applied ESD voltage exceeds the diamond **608**, the ESD current increases slightly in proportion to the applied ESD voltage until the ESD voltage reaches a diamond **610**. The gradual slope from the diamond **608** to the diamond **610** indicates the current path has a high resistance, which is not a desired characteristic for an ESD protection circuit. Once the ESD voltage exceeds 70V, the conventional ESD protection circuit has a sharp snapback where the voltage across the conventional ESD protection circuit drops to a low voltage level (e.g., approximately 7V as shown in FIG. 6). This low voltage indicates that the conventional ESD protection circuit may be permanently damaged.

By contrast, the curve **602** illustrates an advantage of the ESD protection circuit **500**. The isosceles triangles on the curve **602** indicate the I-V relationship of the ESD protection circuit **500**. An isosceles triangle **606** as shown in FIG. 6 indicates the breakdown voltage of the ESD protection circuit **500**. After a resulting breakdown, the curve **602** bends back. As a result, the ESD current grows exponentially. In FIG. 6, the ESD current can be up to 3 A. At the same time, the ESD protection circuit **500** has a relatively high holding voltage (e.g., 20V when the ESD current is 3 A). In sum, the ESD protection circuit **500** provides a high ESD current path as well as a relatively high ESD holding voltage. Both features are beneficial to a reliable ESD protection circuit.

FIG. 7 illustrates an integrated circuit level ESD protection diagram. An integrated circuit chip **700** has a VDD pad **708**, an I/O pad **706** and a VSS pad **704**. Internal circuits **702** are coupled to the VDD pad **708** and VSS pad **704**. The internal circuits **702** further include an input coupled to the I/O pad **706**. In accordance with an embodiment, both the ESD protection circuit **200** and the ESD protection circuit **500** are coupled between the I/O pad **706** and the VSS pad **704**. It should be noted that either the ESD protection circuit **200** or the ESD protection circuit **500** is capable of protecting the internal circuits **702**. Both are provided in FIG. 7 for illustrative purpose only.

When an ESD event occurs between the I/O pad **706** and the VSS pad **704**, either the ESD protection circuit **200** or the ESD protection circuit **500** conducts the ESD current, and the turn-on of an ESD protection circuit (e.g., the ESD protection circuit **200**) clamps the voltage between the I/O pad **706** and the VSS pad **704** below the maximum voltage to which the internal circuits **702** are specified, so that the internal circuits **702** coupled between the I/O pad **706** and the VSS pad **705** are

protected. An advantageous feature of the described circuit level ESD protection is the ESD protection circuit provides a bypass for ESD current to flow so that the internal circuits are protected.

It should be noted that both the ESD protection circuit **200** and the ESD protection circuit **500** may be coupled between the VDD pad **708** and the VSS pad **704** as indicated by the dashed lines in FIG. 7. When an ESD event occurs between the VDD pad **708** and the VSS pad **704**, the conduction of an ESD protection circuit clamps the voltage between the VDD pad **708** and the VSS pad **704**, so that the internal circuits such as internal circuits **702** are protected. In short, the connection of ESD devices **200** and **500** in FIG. 7 is merely an example, which should not unduly limit the scope of the claims. One skilled in the art will recognize many variations, alternatives, and modifications.

FIG. 8 illustrates a further ESD protection scheme by employing a plurality of ESD protection circuits in series connection between an I/O pad and a VSS pad. Similar to FIG. 7, FIG. 8 includes an integrated circuit **700**, a VDD pad **708**, an I/O pad **706**, a VSS pad **704** and internal circuits **702**. However, FIG. 8 further includes a series connection of ESD protection circuits electrically coupled to the I/O pad **706** and the VSS pad **704**. In high voltage applications, a single ESD protection circuit such as the ESD protection circuit **200** shown in FIG. 7 may not provide a reliable ESD protection. By contrast, a plurality of ESD protection circuits **200** in series connection may provide an adjustable ESD protection breakdown point as well as an adjustable ESD protection holding voltage.

In FIG. 8, if an ESD event occurs, a voltage spike is applied between the I/O pad **706** and the VSS pad **704**. The series-connected ESD protection circuits may turn on nearly simultaneously. Each ESD protection circuit provides an ESD protection holding voltage. The sum of all series-connected ESD protection circuits' breakdown voltages clamps the I/O pad's voltage **706** to a level below the maximum rating voltage of the internal circuits **702**, so that the internal circuits **702** are protected.

As described above with respect to FIG. 7, placing ESD devices between the I/O pad **706** and the VSS pad **704** in FIG. 8 is merely an example. One skilled in the art will recognize many variations, alternatives, and modifications, such as connecting ESD devices between the VDD pad **708** and VSS pad **704** as indicated by the dashed lines in FIG. 8.

In the embodiments, by disposing a high voltage P type implanted region underneath a N+ region, an ESD protection circuit provides a reliable ESD protection path as well as a higher ESD breakdown voltage.

In accordance with an embodiment, an ESD protection device has a diode having an anode electrically coupled to a first terminal of a semiconductor device having a breakdown characteristic. The diode further comprises a junction formed by a high voltage P type implanted region and a N+ region disposed on top of the high voltage P type implanted region. When a voltage across the ESD protection device exceeds the sum of the diode and semiconductor device's breakdown voltages, a current may flow through an ESD path formed by the diode and the semiconductor device.

In accordance with another embodiment, an ESD protection structure includes a high voltage N well, a high voltage P type implanted region which is disposed on top of the high voltage N well and partially within the high voltage N well and a first N+ region sequentially disposed on top of the high voltage P type implanted region. The structure further comprises a P+ region disposed on top of the high voltage N well and a second N+ region disposed on top of the high voltage N

well. In the ESD protection structure, the first N+ region and the high voltage P type implanted region form a Zener diode and the Zener diode has a breakdown voltage between 5 and 7V. Furthermore, the high voltage P type implanted region, the high voltage N well and the P+ region form a bipolar PNP transistor. The bipolar PNP transistor is series-connected with the Zener diode to form an ESD protection circuit.

In accordance with yet another embodiment, an ESD protection structure comprises a N+ buried layer; a high voltage N well disposed on top of the N+ buried layer, a high voltage P type implanted region disposed on top of the high voltage N well and partially within the high voltage N well. The structure further comprises a first N+ region sequentially disposed on top of the high voltage P type implanted region, a high voltage P well disposed on top of the N+ buried layer, a second N+ region disposed on top of the high voltage P well and a P+ region disposed on top of the high voltage P well. In the structure, the first N+ region and the high voltage P type implanted region form a reverse diode and the reverse diode has a breakdown voltage. Furthermore, the high voltage P type implanted region, the high voltage N well and the high voltage P well form a bipolar PNP transistor; the high voltage N well, the high voltage P well and the second N+ region form a bipolar NPN transistor. The bipolar PNP transistor and the bipolar NPN transistor form a silicon-controlled rectifier (SCR). The SCR and the reverse diode in series connection form an ESD protection circuit.

Although the present invention and its advantages have been described in detail, it should be understood that various changes, substitutions and alterations can be made herein without departing from the spirit and scope of the invention as defined by the appended claims.

Moreover, the scope of the present application is not intended to be limited to the particular embodiments of the process, machine, manufacture, composition of matter, means, methods and steps described in the specification. As one of ordinary skill in the art will readily appreciate from the disclosure of the present invention, processes, machines, manufacture, compositions of matter, means, methods, or steps, presently existing or later to be developed, that perform substantially the same function or achieve substantially the same result as the corresponding embodiments described herein may be utilized according to the present invention. Accordingly, the appended claims are intended to include within their scope such processes, machines, manufacture, compositions of matter, means, methods, or steps.

What is claimed is:

1. A device comprising:

a high voltage N well and a high voltage P well over an N+ buried layer;
a high voltage P-type implanted region in the high voltage N well;
a first N+ region over the high voltage P-type implanted region; and
a P+ region and a second N+ region over the high voltage P well, wherein the high voltage N well, the high voltage P well, the N+ buried layer, the high voltage P-type implanted region, the first N+ region, the P+ region and the second N+ region form a protection structure comprising a silicon-controlled rectifier and a diode connected in series, wherein an anode of the diode is connected to the silicon-controlled rectifier.

2. The device of claim 1, further comprising:

a first isolation region between the first N+ region and the P+ region; and
a second isolation region between the P+ region and the second N+ region.

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3. The device of claim 1, wherein:
the diode is a reverse diode.
4. The device of claim 1, wherein the silicon-controlled rectifier comprises a PNP transistor and an NPN transistor, and wherein:
the PNP transistor has a base interconnected with a collector of the NPN transistor and a collector interconnected with a base of the NPN transistor.
5. The device of claim 1, wherein:
the diode comprises a cathode formed in the first N+ region and an anode formed in the high voltage P-type implanted region.
6. A structure comprising:
a N+ buried layer;
a high voltage N well disposed on the N+ buried layer;
a high voltage P type implanted region disposed on the high voltage N well and partially within the high voltage N well;
a first N+ region disposed on the high voltage P type implanted region;
a high voltage P well disposed on the N+ buried layer;
a second N+ region disposed on the high voltage P well; and
a P+ region disposed on the high voltage P well, wherein the high voltage N well, the high voltage P well, the N+ buried layer, the high voltage P type implanted region, the first N+ region, the P+ region and the second N+ region form a protection structure comprising a silicon-controlled rectifier and a diode connected in series, wherein an anode of the diode is connected to the silicon-controlled rectifier.
7. The structure of claim 6 further comprising a first isolator, wherein the first N+ region and the P+ region are on opposite sides of the first isolator.
8. The structure of claim 6 further comprising a second isolator, wherein the second N+ region and the P+ region are on opposite sides of the second isolator.
9. The structure of claim 6, wherein:
the first N+ region and the high voltage P type implanted region form a reverse diode having a breakdown voltage.
10. The structure of claim 6, wherein:
the high voltage P type implanted region, the high voltage N well and the high voltage P well form a bipolar PNP transistor; and

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- the high voltage N well, the high voltage P well and the second N+ region form a bipolar NPN transistor.
11. The structure of claim 10, wherein:
the bipolar PNP transistor and the bipolar NPN transistor form the silicon-controlled rectifier.
12. A device comprising:
a diode having a cathode formed in a first N+ region and an anode formed in a high voltage P-type implanted region, wherein the high voltage P-type implanted region is in a high voltage N well over an N+ buried layer; and
a silicon-controlled rectifier comprising a PNP transistor and an NPN transistor, wherein the PNP transistor comprises:
a base interconnected with a collector of the NPN transistor;
a collector interconnected with a base of the NPN transistor; and
an emitter interconnected with the anode of the diode.
13. The device of claim 12, wherein:
the base of the PNP transistor is formed in the high voltage N well;
the collector of the PNP transistor is formed in a high voltage P well and a P+ region, wherein the P+ region is over the high voltage P well; and
an emitter of the NPN transistor is formed in a second N+ region over the high voltage P well.
14. The device of claim 13, wherein:
the high voltage P well is over the N+ buried layer.
15. The device of claim 14, further comprising:
a first isolation region having a first portion over the high voltage N well and a second portion over the high voltage P well; and
a second isolation region over the high voltage P well.
16. The device of claim 15, wherein:
the first N+ region and the P+ region are separated by the first isolation region; and
the P+ region and the second N+ region are separated by the second isolation region.
17. The device of claim 12, wherein:
the silicon-controlled rectifier and the diode are connected series.
18. The device of claim 17, wherein:
the diode is a reverse diode.

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